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Kind regards,

Team Nexperia



PBSS5130T

30 V; 1 A PNP low VCEsat (BISS) transistor

9 July 2013

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Small SMD plastic package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · Higher efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	220	mΩ





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	<u> </u>	C
2	Е	emitter		В—
3	С	collector	1 2	'`
			TO-236AB (SOT23)	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5130T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PBSS5130T	%3E

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-30	V
V_{CEO}	collector-emitter voltage	open base		-	-30	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	Α
I _{BM}	peak base current			-	-300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance	in free air	[1]	-	-	417	K/W
	from junction to ambient		[2]	-	-	260	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

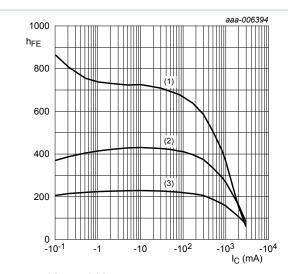
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	300	450	-	
		V_{CE} = -2 V; I_{C} = -500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	260	350	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	210	290	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -100 mA; I_{B} = -1 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-100	mV
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-225	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	220	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-	-0.75	V
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	200	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	28	pF

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$$V_{CE}$$
 = -2 V

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 1. DC current gain as a function of collector current; typical values

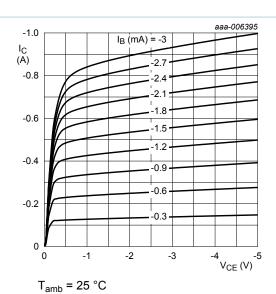
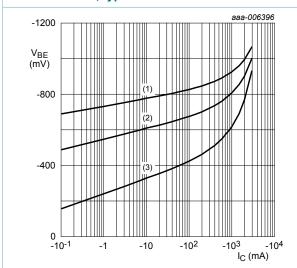


Fig. 2. Collector current as a function of collectoremitter voltage; typical values



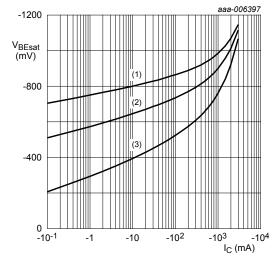
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 3. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

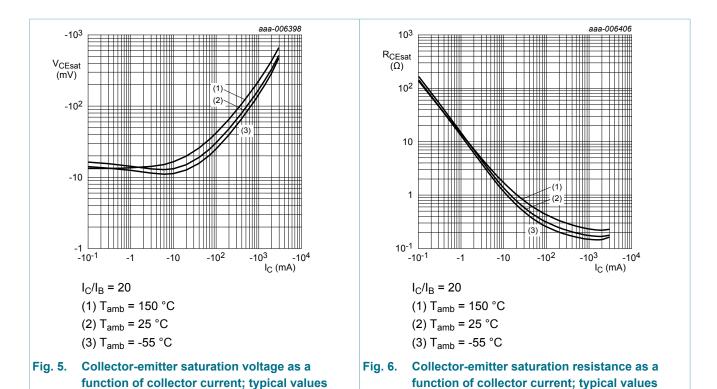
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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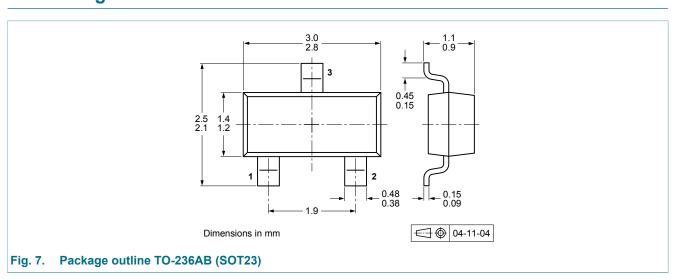


11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



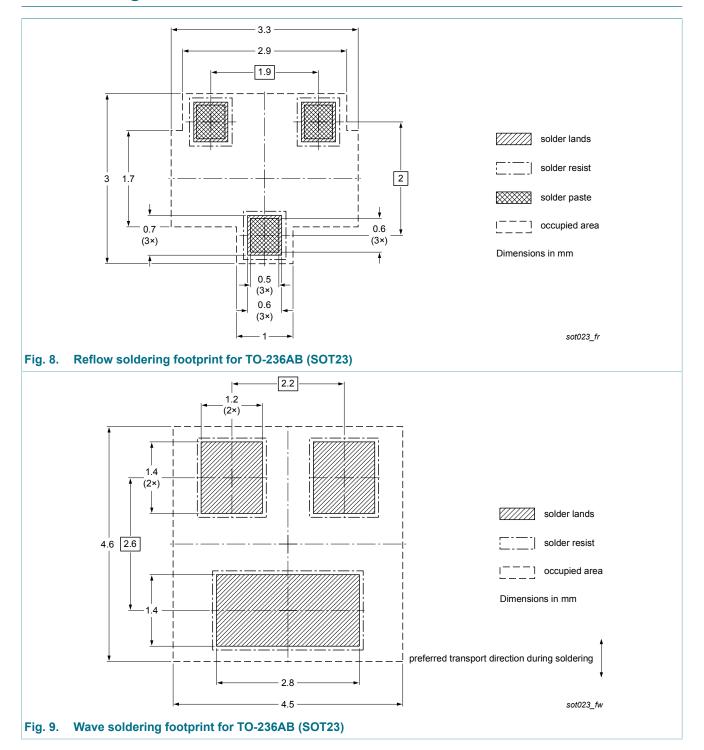
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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5130T v.2	20130709	Product data sheet	-	PBSS5130T v.1
Modifications:	of NXP Semicondu Legal texts have be Sections "General Section "Marking": Table "Limiting valu Table "Characterist Figures 1 to 6: add Section "Test inforr	een adapted to the new condescription", "Features and updated uses": ambient temperature tics": base-emitter saturation and the mation and the condescription an	ompany name where app nd benefits" and "Applicat e T _{amb} updated ion voltage V _{BEsat} added	propriate. tions": updated
PBSS5130T v.1	20031212	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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